N-Channel 60-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- Fast switching speed

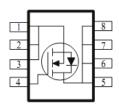
Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
60	50 @ V _{GS} = 10V	6.4		
60	60 @ V _{GS} = 4.5V	5.9		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Symbol	Limit	Units	
Drain-Source Voltage				60	V	
Gate-Source Voltage				±20	V	
Continuous Dusin Comment ^a		T _A =25°C	1	6.4	А	
Continuous Drain Current ^a		T _A =70°C	I _D	5.2		
Pulsed Drain Current ^b	I_{DM}	30				
Continuous Source Current (Diode Conduction) ^a		I _S	4	Α		
Down Dissipation ^a		T _A =25°C	P _D	3.1	W	
Power Dissipation ^a		T _A =70°C	ı D	2		
Operating Junction and Storage Temperature Range			T_J, T_{sta}	-55 to 150	°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	40	°C/W		
IVIAXIIIIUIII JUIICIIOII-IO-AIIIDIEIII	Steady State	'`ӨЈА	80			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

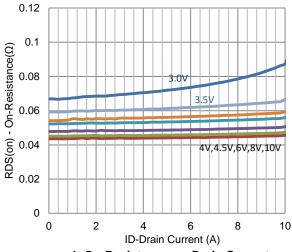
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}$			1	· uA I	
Zero Gate Voltage Brain Gurrent	טטי	$V_{DS} = 48 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_D = 5.1 \text{ A}$			50	mΩ	
Dialii-Source Off-Nesistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 5 \text{ A}$			60	11177	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 5.1 \text{ A}$		40		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 2 \text{ A}, V_{GS} = 0 \text{ V}$		0.77		V	
		Dynamic					
Total Gate Charge	Q_g			3.8		nC	
Gate-Source Charge	Q_gs	$V_{DS} = 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 5.1 \text{ A}$		1.6			
Gate-Drain Charge	Q_{gd}			1.4			
Turn-On Delay Time	t _{d(on)}			3			
Rise Time	t _r	$V_{DD} = 30 \text{ V}, R_L = 5.9 \Omega, I_D = 5.1 \text{ A},$ $V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		4			
Turn-Off Delay Time	$t_{d(off)}$			18		ns	
Fall Time	t _f			5			
Input Capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		382		pF	
Output Capacitance	C _{oss}			58			
Reverse Transfer Capacitance	C _{rss}			32			

Notes

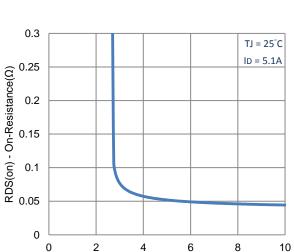
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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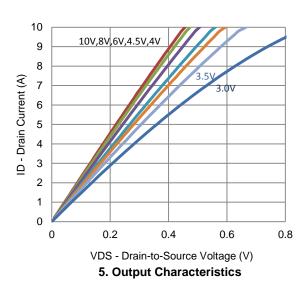
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current

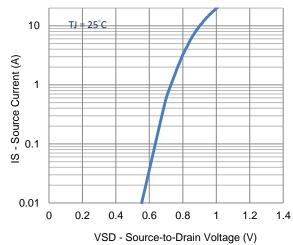


VGS - Gate-to-Source Voltage (V)
3. On-Resistance vs. Gate-to-Source Voltage

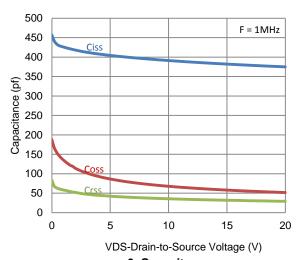


15 TJ = 25° 14 13 12 ID - Drain Current (A) 11 10 9 8 7 6 5 4 3 2 1 0 2 3 4 0 5 VGS - Gate-to-Source Voltage (V)

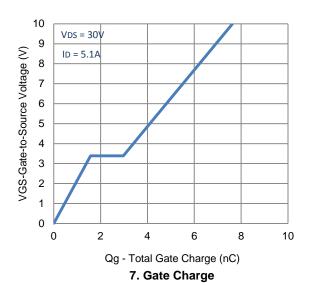
2. Transfer Characteristics

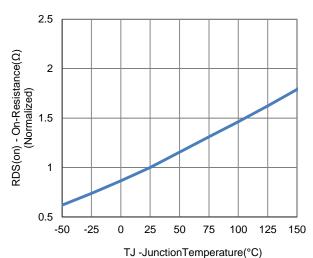


4. Drain-to-Source Forward Voltage

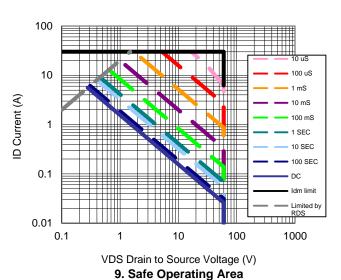


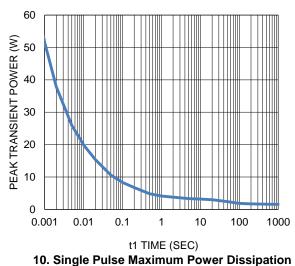
Typical Electrical Characteristics

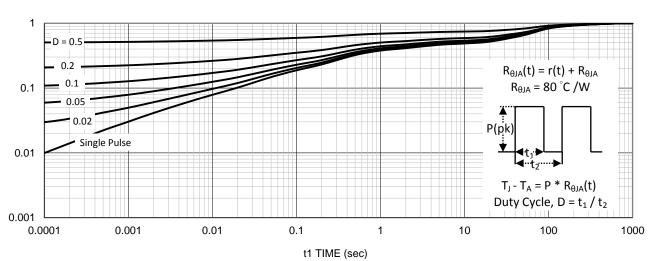




8. Normalized On-Resistance Vs Junction Temperature



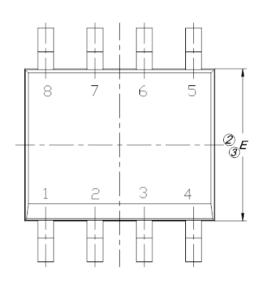


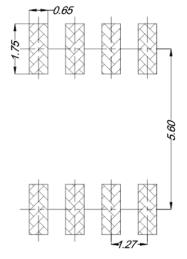


11. Normalized Thermal Transient Junction to Ambient

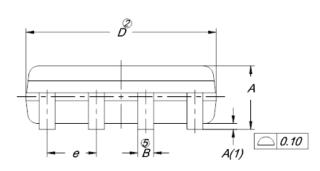
Package Information

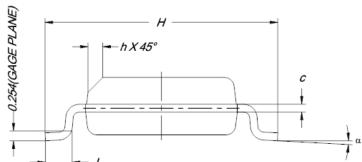
Land Pattern (Only for Reference)





DII.4	MILLIMETERS					
DIM.	MIN.	NOM.	MAX.			
Α	1.35	1.55	1.75			
A(1)	0.10	0.18	0.25			
В	0.38	0.45	0.51			
С	0.19	0.22	0.25			
D	4.80	4.90	5.00			
E	3.80	3.90	4.00			
е	1.27 BSC					
Н	5.80	6.00	6.20			
L	0.50	0.72	0.93			
α	0°	4°	8°			
h	0.25	0.38	0.50			





Note:

- 1. All Dimension Are In mm.
- 2. Package Body Sizes Exclude Mold Flash, Protrusion Or Gate Burrs. Mold Flash, Protrusion Or Gate Burrs Shall Not Exceed 0.10 mm Per Side.
- 3. Package Body Sizes Determined At The Outermost Extremes Of The Plastic Body Exclusive Of Mold Flash, Tie Bar Burrs, Gate Burrs And Interlead Flash, But Including Any Mismatch Between The Top And Bottom Of The Plastic Body.
- 4. The Package Top May Be Smaller Than The Package Bottom.
- Dimension Br Does Not Include Dambar Protrusion. Allowable Dambar Protrusion Shall Be 0.08 mm Total In Excess
 Of Br Dimension At Maximum Material Condition. The Dambar Cannot Be Located On The Lower Radius Of The
 Foot.

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